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ELD-850-525

- INFRARED Light Emitting Diode
- 850 nm, 11 mW
- AlGaAs, DDH
- 5 mm epoxy package



Description

ELD-850-525 is an AlGaAs DDH infrared LED, typically emitting at 850 nm with an optical output power of 11 mW. It comes in a hermetically sealed clear 5 mm epoxy resin.

Maximum Rating ($T_{CASE} = 25^\circ\text{C}$)

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation, DC	P_D		200	mW
Forward Current	I_{FM}		150	mA
Pulse Forward Current*	I_{FP}		200	mA
Operating Temperature	T_{OPR}	- 20	+ 80	°C
Storage Temperature	T_{STG}	- 40	+ 85	°C
Soldering Temperature (max 3s)	T_{SOL}		+ 260	°C
Junction Temperature	T_J		100	°C

* $t_p \leq 50 \mu\text{s}, t_p/T = 1/2$

Electro-Optical Characteristics ($T_{CASE} = 25^\circ\text{C}, I_F = 20 \text{ mA}$)

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Peak Wavelength	λ_P	840	850	860	nm
Spectral Width (FWHM)	$\Delta\lambda$		40		nm
Forward Voltage @ 20 mA	V_F		1.4	1.6	V
Forward Voltage @ 100 mA	V_F		1.6	2.0	V
Reverse Voltage ($I_R = 10 \mu\text{A}$)	V_R	5			V
Radiant Power @ 20 mA	Θ_e	7	11		mW
Radiant Power @ 100 mA	Θ_e		45		mW
Switching time	t_R, t_F		10, 20		ns
Viewing Half Angle	$\Theta_{1/2}$		10		deg.

